PROCEEDINGS OF SPIE

International Conference on Microand Nano-Electronics 2018

Vladimir F. Lukichev Konstantin V. Rudenko Editors

1–5 October 2018 Zvenigorod, Russian Federation

Organized by Valiev Institute of Physics and Technology of Russian Academy of Sciences (Russian Federation) JSC "Molecular Electronics Research Institute" (Russian Federation)

Sponsored by Russian Foundation for Basic Researches (Russian Federation) Russian Academy of Sciences (Russian Federation) Technolnfo Ltd. (United Kingdom/Russian Federation) NIX Company (Russian Federation)

Published by SPIE

Volume 11022

Proceedings of SPIE 0277-786X, V. 11022

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Author(s), "Title of Paper," in International Conference on Micro- and Nano-Electronics 2018, edited by Vladimir F. Lukichev, Konstantin V. Rudenko, Proceedings of SPIE Vol. 11022 (SPIE, Bellingham, WA, 2019) Seven-digit Article CID Number.

ISSN: 0277-786X ISSN: 1996-756X (electronic)

ISBN: 9781510627093 ISBN: 9781510627109 (electronic)

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Contents

- xi Authors
- xv Conference Committee
- xxi Introduction

PHYSICS OF MICRO- AND NANODEVICES

- Barrier-injection transit-time diodes and transistors for terahertz generation and detection (Invited Paper) [11022-106]
 Plasmonic terahertz emitters with high-aspect ratio metal gratings [11022-18]
 Silver-based double metal waveguide for terahertz quantum cascade laser [11022-35]
- 11022 05 **Tunnel undoped multiple-gate field-effect transistor with Schottky contacts** [11022-107]
- 11022 06 **Development of a molecular single-electron transistor with a single-atom charge center** [11022-77]
- 11022 07 Charge effects in dielectric films of MIS structures being under high-field injection of electrons at ionizing radiation [11022-56]
- 11022 08 Formation of surface states in MOS devices by space radiation protons [11022-79]
- 11022 09 Nanoscale planar ring-shaped matrix field emitters based on multilayer graphene/SiC [11022-90]
- 11022 0A Experimental study of a broadband vacuum photosensor with the tunnel emission from a metal nanoscale blade [11022-32]
- 11022 0B Static and dynamic spin-torque-diode sensitivity induced by the thermoelectric charge and spin currents in magnetic tunnel junctions [11022-114]
- 11022 0C Scalability analysis of magnetic-nano-junction-based STT-MRAM towards sub-20-nm technology nodes [11022-102]
- 11022 0D Investigations of the resistive switching of the TiN-TiO₂-SiO₂-W memristors in the oxygen atmosphere with varying pressure [11022-5]
- 11022 OE Nanoscale profiling and memristor effect of ZnO thin films for RRAM and neuromorphic devices application [11022-74]

DEVICE MODELING AND SIMULATION 11022 OF Simulation of graphene field-effect transistors and resonant tunneling diodes based on carbon nanomaterials [11022-10] 11022 0G Modeling of the submicron MOSFETs characteristics for UTSi technology [11022-65] 11022 OH A linear "extrinsic" compact model for short-channel MOSFET drain current asymptotic dependence on drain bias in saturation regime [11022-46] 11022 OI Compact modeling of electrical characteristics of p-MNOS based RADFETs [11022-29] 11022 OJ A novel approach to model high-speed microelectronic switch on the basis of hydrodynamic approximation [11022-30] 11022 OK Quasi-hydrodynamic numerical model of high-speed on-chip photodetectors for optical interconnections [11022-47] 11022 OL Efficiency of terahertz harmonic generation in GaAs quantum wire structure: a Monte Carlo **simulation** [11022-21] Arrays of several Josephson junctions connected to oscillatory circuit [11022-23] 11022 OM 11022 ON Simulation of single-electron transistor based on the molecule with single-atom charge center [11022-45] 11022 0O TCAD-based performance analysis of nanoscale vacuum field-emission transistors at advanced technology nodes [11022-104] MEMS DEVICES AND SENSORS 11022 OP A low actuation voltage MEMS switch with protection against stiction [11022-11] Research of the microelectromechanical switch with different materials of metal membrane 11022 0Q [11022-20]

- 11022 ORFinite-element predictive 3D modelling and optimization of membrane-based thermoresistive
MEMS accelerometers [11022-110]
- 11022 0S ANSYS simulation of the microaccelerometer sensor [11022-36]
- 11022 0T Automated approach to the analysis of geometric parameters of MEMS elements [11022-57]
- 11022 0U Research and analysis of heat exchange processes of a micromechanical mirror based on a thermal microactuator [11022-6]

11022 0V Silicon nanobridge as a high quality mechanical resonator [11022-13]

- 11022 0W Determination of vibration axes of the micromachined ring resonator for the modal tuning purposes [11022-14]
- 11022 0X Improving the selectivity of carbon nanotube-based gas sensors via UV irradiation [11022-91]
- 11022 0Y Hybrid acousto-nano-biosensor [11022-39]
- 11022 0Z Thyroglobulin detection by biosensor based on two independent Si NW FETs [11022-97]
- 11022 10 High-sensitive ultra-low frequency hydrophone [11022-60]
- 11022 11 Influence of the electromigration on the characteristics of electrochemical microsystems [11022-54]

MICRO- AND NANOELECTRIC MATERIALS AND FILMS

- 11022 12 Silicon oxides and silicon nitrides: structure, properties and applications in memristors [11022-33]
- 11022 13 Swift heavy ion stimulated formation of the Si quantum dots in Si/SiO₂ multilayer heterostructures [11022-71]
- 11022 14 Luminescent properties of GeO_x thin films and GeO/SiO₂ heterostructures modified with swift heavy ions [11022-28]
- 11022 15 The manifestation of rising of the impurity density of states after the field stress in increasing of the effective electron mobility in the inversion channel at the silicon-oxide contact [11022-44]
- 11022 16 Features of the field damage of ultra-thin insulating layers of the silicon oxide [11022-43]
- 11022 17 Fabrication technology of sol-gel Al₂O₃ films for organic field-effect transistors [11022-69]
- 11022 18 Influence of power and pulsed regime of low frequency discharge on clusters incorporation in dielectric films for ReRAM application [11022-37]
- 11022 19 Structural and morphological properties of Ga(Al)N grown by MBE on 3C-SiC/Si (111) templates with off-axis and on-axis substrate orientation [11022-50]
- 11022 1A Laser reduction of graphene oxide thin films for nanoelectronic application [11022-41]
- 11022 1B Effects of vacuum-plasma etching on the electrical properties of thin ferroelectric PZT films [11022-8]
- 11022 1C Electric-field-induced domain switching and pinning state in lead-free ferroelectric BST 80/20 film [11022-42]

11022 1D	Formation features and electrophysical properties of ferroelectric films ZnO study [11022-53]
11022 1E	Influence of annealing on nanocrystalline LiNbO3 films properties [11022-73]
11022 1F	Electronic and optical properties of MoS_2 thin films deposited by magnetron sputtering studying [11022-1]
11022 1G	Nanocrystalline diamond films heavily doped by boron: structure, optical and electrical properties [11022-25]
11022 1H	Concept of glass formation in chalcogenide systems and the possibility of predicting new compounds for micro- and nanoelectronics [11022-31]
11022 11	The opportunities of Rutherford backscattering spectroscopy for analysis of multilayer nanometer thin film structures [11022-66]
11022 1J	Effect of mechanical deformations on absorption spectrum of metallic films of nanometer thickness [11022-51]
11022 1K	Different magnetooptical properties of metallized nanostructured arrays on silicon surface [11022-4]
11022 1L	Energetics of domain wall in magnetic nanowire [11022-19]

MICRO- AND NANOELECTRONIC TECHNOLOGIES I

- 11022 1M Maskless nanolithography on the basis of microfocus x-ray tubes: conversion of electron energy into the BeKa line (Invited Paper) [11022-67]
- 11022 1N Cellular automata method for directed self-assembly modeling [11022-103]
- 11022 10 Simulation of dry e-beam etching of resist and experimental evidence [11022-96]
- 11022 1P Fabrication of electrodes for a logic element based on a disordered dopant atoms network [11022-105]
- 11022 10 Formation of nanosized elements by ion beam lithography for multiple fin field effect transistor prototyping [11022-68]
- 11022 1R Mask formation on GaAs substrate by focused ion beams of Ga⁺ for plasma chemical etching [11022-75]
- 11022 15 Methods and means of experimental investigation of gas-phase deposition of material layers in MEMS processes [11022-7]
- 11022 1T Synergistic effects of deformation and solid state reactions in Si with buried glass layer initiated by annealing in non-isothermal reactor [11022-22]

11022 1U	Induced bistability into quartz glass by silicon wafer heat treatment in lamp-based reactor [11022-48]
11022 1V	Localization of a thermo-optical traveling wave at an optical inhomogeneity in a silicon wafer under lamp-based heating [11022-24]
11022 1W	Investigation of technological operations for manufacturing 3D micro-assemblies with embedded elements [11022-40]
	MICRO- AND NANOELECTRONIC TECHNOLOGIES II
11022 1X	Deep silicon plasma etching: selection of processes for different applications (Invited Paper) [11022-109]
11022 1Y	Sidewall defects in deep cryogenic Si etching in SF ₆ /O ₂ plasma: a numerical simulation [11022-83]
11022 1Z	Features of silicon deep plasma etching process at 3D-TSV structures producing [11022-52]
11022 20	Effect of the sublayer material on the formation of electrical contact and the growth rate of carbon nanotubes in a low-temperature plasma using the example of Ni/Ti/Si and Fe/W/Si structures [11022-76]
11022 21	Formation of metallic nanowire and nanonet structures on the surface of SiO ₂ by combine plasma etching processes [11022-16]
11022 22	Fabrication and properties of SOI-based planar silicon nanowire arrays [11022-95]
11022 23	Effect of Ar ion-plasma treatment on residual stress in thin Cr films [11022-26]
11022 24	Plasma deposition of carbon-silicon nanocomposite for microelectromechanical applications [11022-61]
11022 25	Cyclic discrete etching of Silicon oxide in deposition-sputtering cycles: towards to ALE [11022-99]
11022 26	Study of synergy phenomena for atomic layer etching of aluminum and hafnium oxides [11022-100]
11022 27	Optical emission spectra of BF3/Ar-plasma: detection of the boron 563.3-nm spectral line and identification of BF band spectra [11022-72]
	QUANTUM INFORMATICS I
11022 28	Broadband impedance matching in white cavity (Invited Paper) [11022-94]

11022 29 **Robust random number generator based on field effect transistor** [11022-89]

11022 2A	Quantum computer based on triangular atom-photon molecule [11022-92]
11022 2B	Multi-qubit controlled NOT gates for artificial intelligence natural languages processing [11022-93]
11022 2C	Homogeneous atomic ensembles and single-mode field: review of simulation results (Invited Paper) [11022-34]
11022 2D	Quantum lock on dark states (Invited Paper) [11022-116]
11022 2E	Multiple quantum coherence transfer and quantum correlations in NMR experiments in solids [11022-3]
11022 2F	Quantum entanglement in trimer clusters [11022-2]
11022 2G	Quantum entanglement in spin chains with the XY Hamiltonian at the quantum state transfer [11022-27]
11022 2H	Quantum information processing with macroscopic two-component Bose-Einstein condensates [11022-88]
11022 21	Jumps of optimal measurement angle and fractures on the curves of quantum correlation functions [11022-17]

11022 2J Hitting time for quantum walks of identical particles [11022-55]

QUANTUM INFORMATICS II

11022 2K	Multiphoton subtracted thermal states: description, preparation, measurement and utilization [11022-64]
11022 2L	Theoretical and experimental study of multi-mode thermal states with subtraction of a random number of photons [11022-49]
11022 2M	Quantum tomography based on principles of completeness, adequacy and fidelity [11022-86]
11022 2N	High-fidelity quantum tomography with imperfect measurements [11022-82]
11022 20	The concept of weak measurements and the super-efficiency of quantum tomography [11022-63]
11022 2P	On the fidelity of quantum gates under T1 and T2 relaxation [11022-78]
11022 2Q	Quantum approach to the dynamical systems modeling [11022-84]
11022 2R	Representation of Boolean functions in terms of quantum computation [11022-62]

- 11022 25 Machine learning methods in quantum computing theory [11022-85]
- 11022 2T **Two-way quantum and classical machines with small memory for online minimization** problems [11022-98]
- 11022 20 Molecule ground state energy estimation via continuous-time quantum walks [11022-101]
- 11022 2V Sequences of selective rotation operators to engineer interactions for quantum annealing on three qutrits [11022-15]
- 11022 2W Fast quantum randomness generation from vacuum fluctuation induced phase diffusion between pulses of laser diode [11022-87]